Amendments to the Claims

Listing of Claims:

1. (Currently Amended) A method of creating a horizontal tip feature in a layer of tip material, comprising:

using an etch process to create an etch feature in the layer of tip material, the etch feature having horizontal areas and a substantially vertical sidewall, and the etch process having a slower etch rate near the substantially vertical sidewall than near the horizontal area; and

stopping the etch process in order to form a portion of the substantially vertical sidewall and a horizontal tip feature adjacent to the portion of the substantially vertical sidewall.

2. (Original) A method according to claim 1, further comprising:

monitoring the progress of the etch process.

3. (Original) A method according to claim 1, further comprising:

depositing the layer of tip material on a substrate material, the substrate material being different than the tip material.

4. (Original) A method according to claim 3, further comprising:

selecting an etch process that is selective to the tip material relative to the substrate material.

5. (Original) A method according to claim 1, further comprising:

varying a rate of polymer generation in order to control the slower etch rate of the etch process.

6. (Original) A method according to claim 1, further comprising:

determining the size of the horizontal tip feature to be created before using the etch process.

7. (Original) A method according to claim 1, further comprising:

controlling the profile of the substantially vertical sidewall.

8. (Original) A method according to claim 1, further comprising:

filling the etch feature with a lens material in order to form a lens having a shape determined by the shape of the etch feature.

9. (Original) A method according to claim 1, further comprising:

positioning a photo-sensitive device adjacent the layer of tip material such that the horizontal tip feature serves as an aperture for the photosensitive device.

10. (Original) A method according to claim 1, further comprising:

placing a photoresist mask over the layer of tip material, the photoresist mask acting as a mask for the etch process.

11. (Original) A method according to claim 10, wherein:

stopping the etch process causes the etch feature to have a critical dimension due to the horizontal tip feature that is less than the minimum dimension of the photoresist mask.

12. (Original) A method according to claim 1, wherein:

using an etch process includes using a reactive ion etch process.

13-20 (Cancelled)